Transistors

General purpose (dual digital transistors) UMB3N / IMB3A

Features

- Two DTA143T chips in a UMT or SMT package.
- Mounting possible with UMT3 or SMT3 automatic mounting machines.
- Transistor elements are independent, eliminating interference.

Structure

Dual PNP digital transistor (each with single built in resistor)

The following characteristics apply to both DTr_1 and DTr_2 .

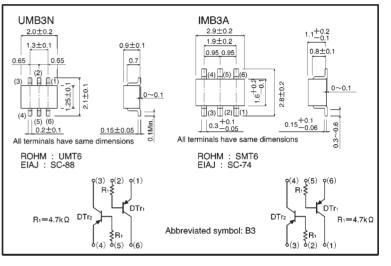
•Absolute maximum ratings (Ta = 25° C)

Parameter		Symbol	Limits	Unit	
Collector-base voltage		V _{CBO}	V _{СВО} —50		
Collector-emitter voltage		VCEO	-50	V	
Emitter-base voltage		V _{EBO} —5		V	
Collector current		lc	lc —100 r		
Collector power dissipation	UMB3N	P	150(TOTAL)	mW	*1
	IMB3A	Pc	300(TOTAL)		*2
Junction temperature		Tj 150 °		Ĵ	
Storage temperature		Tstg	-55~+150	Ĵ	

*1 120mW per element must not be exceeded.

*2 200mW per element must not be exceeded.

External dimensions (Units: mm)





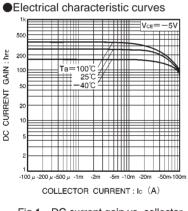
Electrical characteristics (Ta = 25°C)

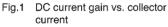
Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Collector-base breakdown voltage	ВV _{CBO}	-50	_	-	V	$I_{\rm C} = -50 \mu \mathrm{A}$
Collector-emitter breakdown voltage	BV _{CEO}	-50	_	_	V	$I_{C}=-1mA$
Emitter-base breakdown voltage	BVEBO	-5	_	-	V	$I_E = -50 \mu A$
Collector cutoff current	Ісво	_	_	-0.5	μA	$V_{CB} = -50V$
Emitter cutoff current	I _{EBO}		_	-0.5	μA	V _{EB} =-4V
Collector-emitter saturation voltage	V _{CE(sat)}	-	—	-0.3	V	I _C /I _B =-5mA/-2.5mA
DC current transfer ratio	h _{FE}	100	250	600	—	V_{CE} =-5V, I _C =-1mA
Transition frequency	fт	_	250	_	MHz	$V_{CE}=10mA, I_{E}=-5mA, f=100MHz*$
Input resistance	R ₁	3.29	4.7	6.11	kΩ	—

* Transition frequency of the device

Packaging specifications

	Packaging type	Тар	bing
	Code	TN	T110
Part No.	Basic ordering unit (pieces)	3000	3000
UMB3N		0	_
IMB3N			0





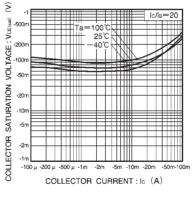


Fig.2 Collector-emitter saturation voltage vs. collector current

